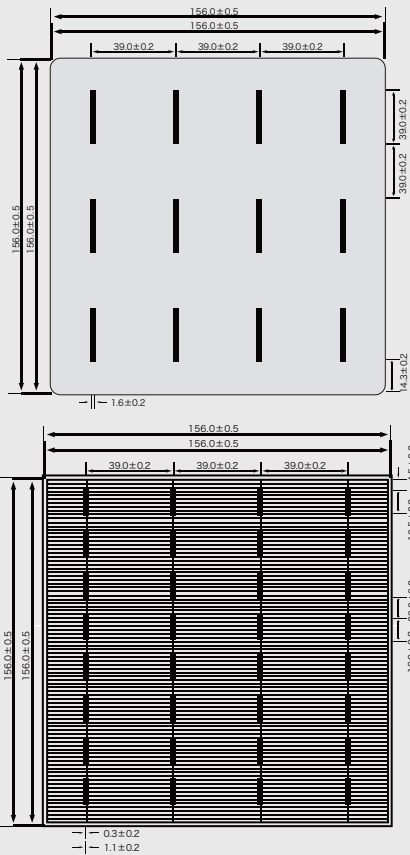


# POLYCRYSTALLINE SILICON CELLS

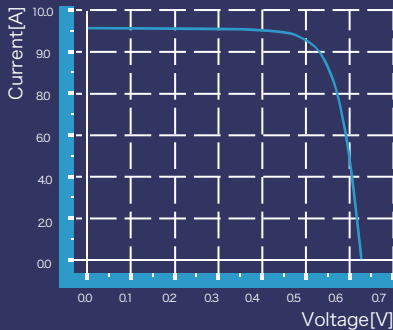
## GSUN156P-4BB



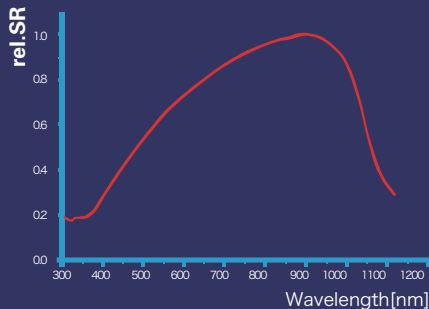
### Polycrystalline Silicon Cells

Model	Efficiency	Power	Min Power Current	Max Power Voltage	Short Circuit Current	Open Circuit Voltage
型号	转换效率	功率	最小工作电流	最大工作电压	短路电流	开路电压
	Eff(%)	Ppm(W)	Ipm(A)	Vpm (V)	Isc(A)	Voc(V)
GSUN156P-4BB01	19.10-20.00	4.65	8.59	0.541	8.97	0.640
GSUN156P-4BB02	19.00-19.10	4.63	8.58	0.539	8.94	0.639
GSUN156P-4BB03	18.90-19.00	4.60	8.54	0.538	8.93	0.638
GSUN156P-4BB04	18.80-18.90	4.58	8.51	0.537	8.92	0.637
GSUN156P-4BB05	18.70-18.80	4.55	8.48	0.536	8.91	0.636
GSUN156P-4BB06	18.60-18.70	4.53	8.46	0.535	8.90	0.635
GSUN156P-4BB07	18.40-18.59	4.48	8.40	0.534	8.89	0.634
GSUN156P-4BB08	18.20-18.39	4.43	8.36	0.532	8.82	0.633
GSUN156P-4BB09	18.00-18.19	4.38	8.26	0.529	8.78	0.630
GSUN156P-4BB10	17.80-17.99	4.33	8.20	0.527	8.74	0.629
GSUN156P-4BB11	17.60-17.79	4.28	8.08	0.524	8.70	0.628

#### IV CURVE



#### SPECTRAL RESPONSE



\*calibrated against fraunhofer ISE freiburg

### GSUN156P

Product :Polycrystalline silicon solar cell

Dimension: 156mm×156mm ±0.5mm

Thickness(Si): 200μm±20μm

Front: Blue silicon nitride antireflection coatings 1.1mm silver busbar

Back: Full-surface aluminum back-surface field 1.6mm(silver/aluminum)continuous or discrete soldering pads

### INTENSITY DEPENDENCE

Intensity(W/m2)	Isc	Voc	Pmpp
1000	1.0	1.00	1.00
800	0.8	0.99	0.79
500	0.5	0.96	0.49
300	0.3	0.93	0.29
200	0.2	0.92	0.19

### TEMPERATURE COEFFICIENTS

TkVoltage -0.35%K

TkCurrent +0.06%K

TkPower -0.42%K

The Parameters are for reference only, which are subject to change without notice or obligation.

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